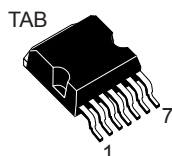
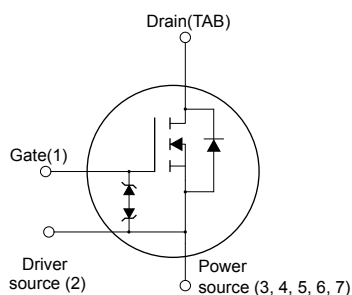


Automotive-grade N-channel 650 V, 102 mΩ typ., 28 A MDmesh DM6 Power MOSFET in an H²PAK-7 package



H²PAK-7



N-chG1DS2PS34567DTABZ



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STH30N65DM6-7AG	650 V	115 mΩ	28 A

- AEC-Q101 qualified 
- Fast-recovery body diode
- Lower R_{DS(on)} per area vs previous generation
- Low gate charge, input capacitance and resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high-voltage N-channel Power MOSFET is part of the MDmesh DM6 fast-recovery diode series. Compared with the previous MDmesh fast generation, DM6 combines very low recovery charge (Q_{rr}), recovery time (t_{rr}) and excellent improvement in R_{DS(on)} per area with one of the most effective switching behaviors available in the market for the most demanding high-efficiency bridge topologies and ZVS phase-shift converters.

Product status link

[STH30N65DM6-7AG](#)

Product summary

Order code	STH30N65DM6-7AG
Marking	30N65DM6
Package	H ² PAK-7
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^{\circ}\text{C}$	28	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^{\circ}\text{C}$	18	A
$I_{DM}^{(1)}$	Drain current (pulsed)	112	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	223	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	100	V/ns
$di/dt^{(2)}$	Peak diode recovery current slope	1000	A/ μ s
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	V/ns
T_J	Operating junction temperature range	-55 to 150	$^{\circ}\text{C}$
T_{stg}	Storage temperature range		$^{\circ}\text{C}$

1. Pulse width limited by safe operating area.
2. $I_{SD} \leq 28\text{ A}$, $V_{DS}(\text{peak}) < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$.
3. $V_{DS} \leq 520\text{ V}$.

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.56	$^{\circ}\text{C/W}$
$R_{thJB}^{(1)}$	Thermal resistance, junction-to-board	30	$^{\circ}\text{C/W}$

1. When mounted on FR-4 board of 1 inch², 2 oz Cu.

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or non-repetitive (pulse width limited by T_J max)	4	A
E_{AS}	Single pulse avalanche energy (starting $T_J = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 100\text{ V}$)	600	mJ

2 Electrical characteristics

$T_C = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Table 4. On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$			5	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 650\text{ V}$, $T_C = 125\text{ }^{\circ}\text{C}^{(1)}$			200	μA
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	3.25	4.00	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 10\text{ A}$		102	115	m Ω

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	2000	-	pF
C_{oss}	Output capacitance		-	130	-	pF
C_{rss}	Reverse transfer capacitance		-	1.5	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{DS} = 0\text{ to }520\text{ V}$, $V_{GS} = 0\text{ V}$	-	339	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$, open drain	-	1.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}$, $I_D = 28\text{ A}$, $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	46	-	nC
Q_{gs}	Gate-source charge		-	13.5	-	nC
Q_{gd}	Gate-drain charge		-	20	-	nC

1. $C_{oss\text{ eq.}}$ is defined as the constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 325\text{ V}$, $I_D = 14\text{ A}$, $R_G = 4.7\text{ }\Omega$, $V_{GS} = 10\text{ V}$	-	17	-	ns
t_r	Rise time		-	3.3	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 13. Switching times test circuit for resistive load and Figure 18. Switching time waveform)	-	46	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		28	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		112	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 28\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 28\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	126		ns
Q_{rr}	Reverse recovery charge		-	0.63		μC
I_{RRM}	Reverse recovery current		-	10		A
t_{rr}	Reverse recovery time	$I_{SD} = 28\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	220		ns
Q_{rr}	Reverse recovery charge		-	2.1		μC
I_{RRM}	Reverse recovery current		-	19		A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

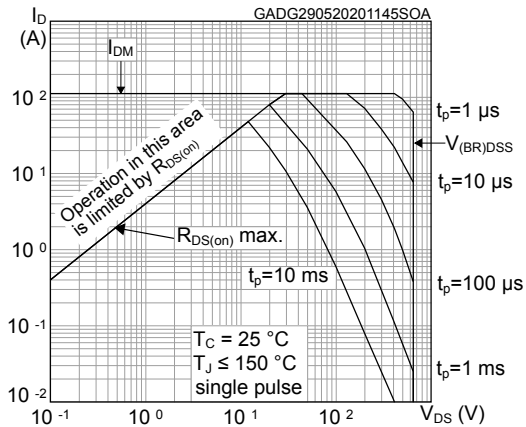


Figure 2. Maximum transient thermal impedance

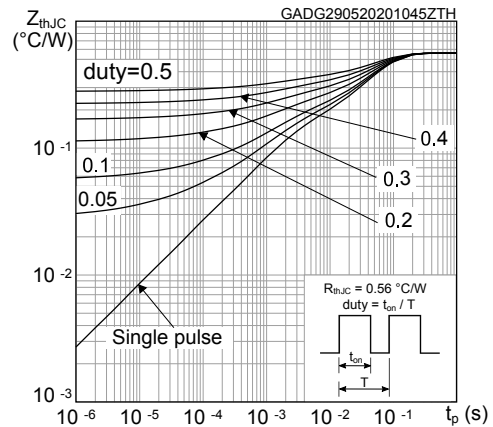


Figure 3. Typical output characteristics

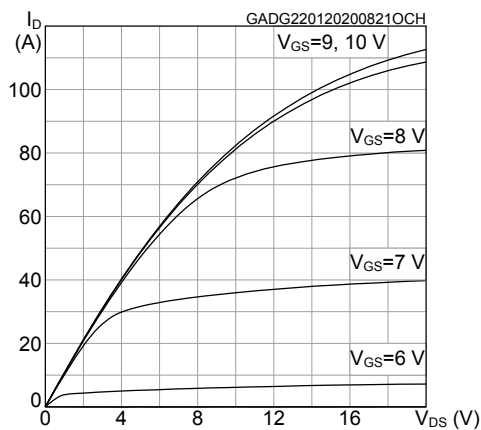


Figure 4. Typical transfer characteristics

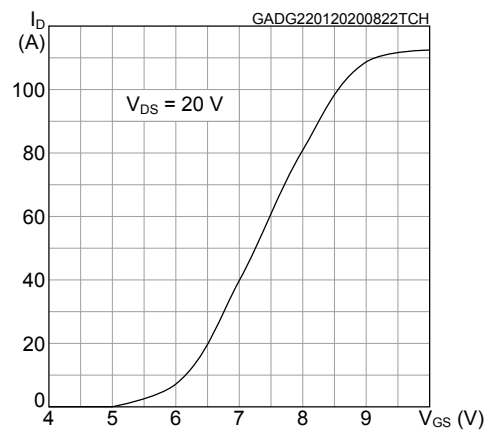


Figure 5. Typical drain-source on-resistance

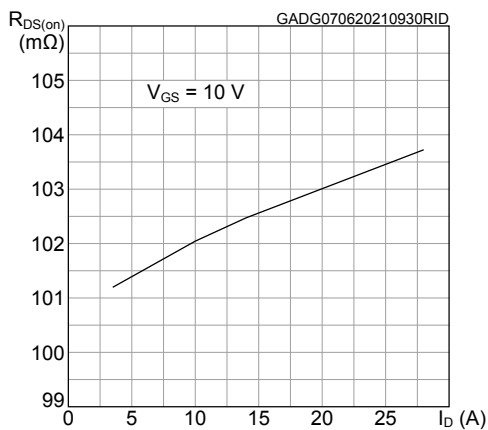


Figure 6. Typical gate charge characteristics

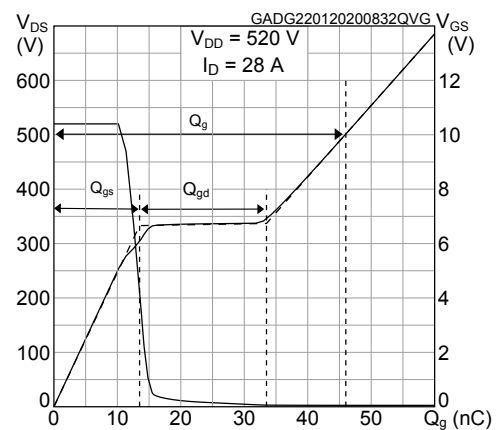


Figure 7. Typical capacitance characteristics

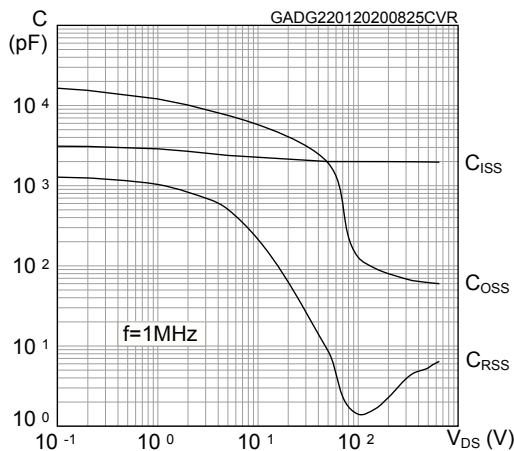


Figure 8. Normalized gate threshold vs temperature

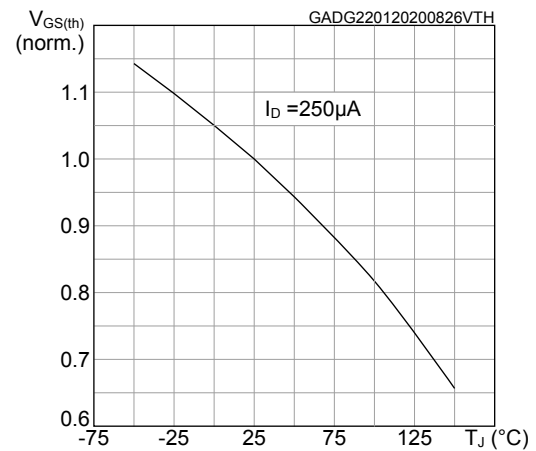


Figure 9. Normalized on-resistance vs temperature

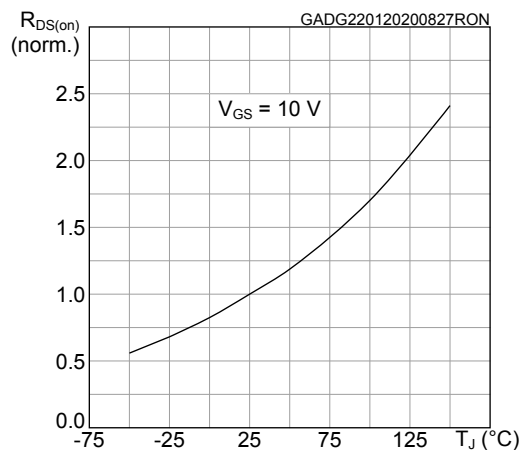


Figure 10. Typical output capacitance stored energy

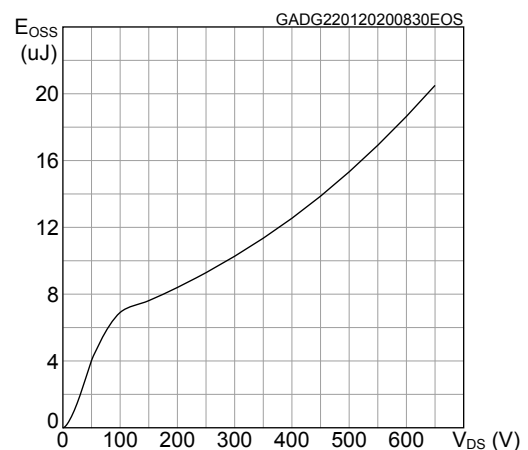


Figure 11. Normalized breakdown voltage vs temperature

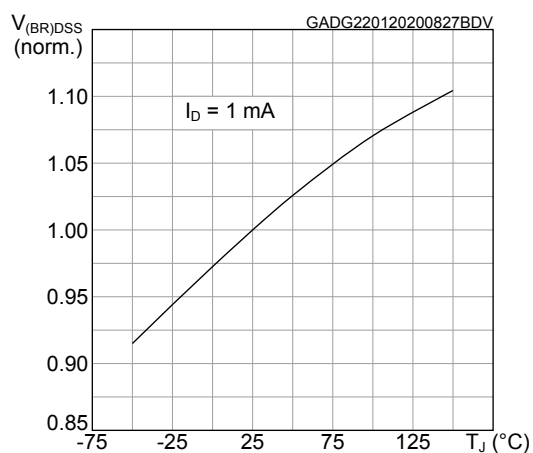
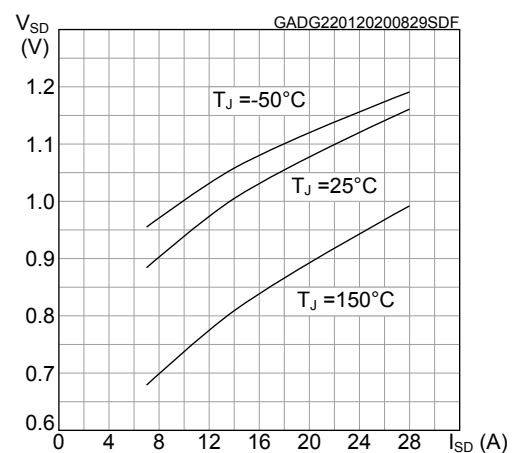
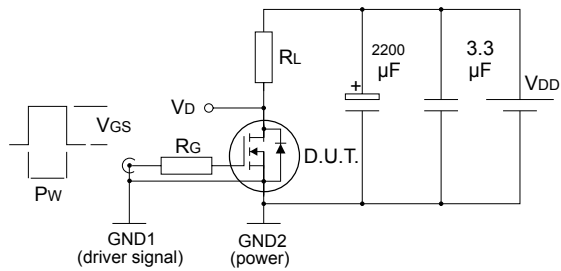


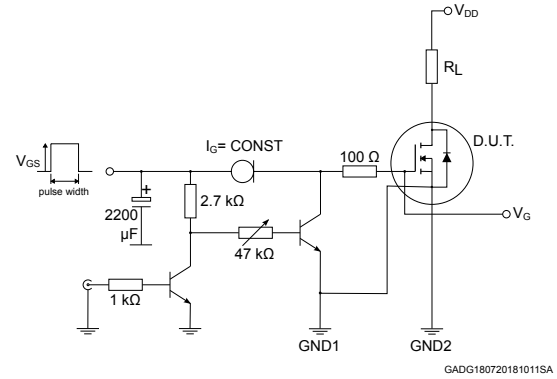
Figure 12. Typical reverse diode forward characteristics



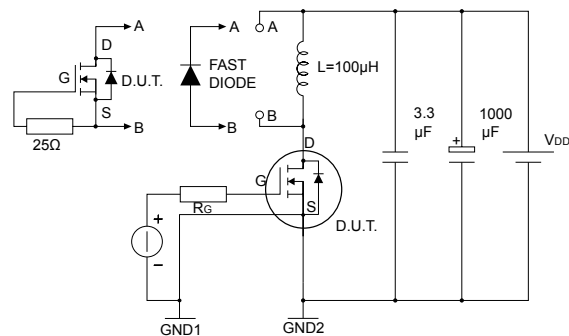
3 Test circuits

Figure 13. Switching times test circuit for resistive load


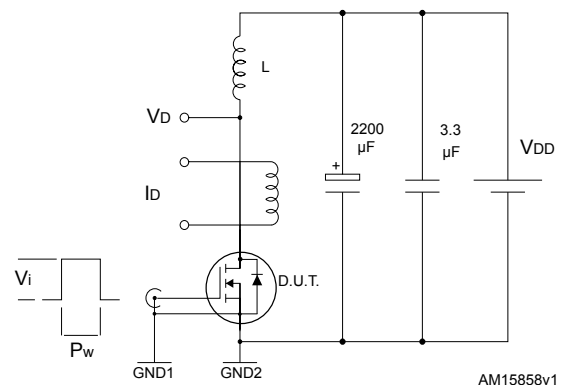
AM15855v1

Figure 14. Test circuit for gate charge behavior


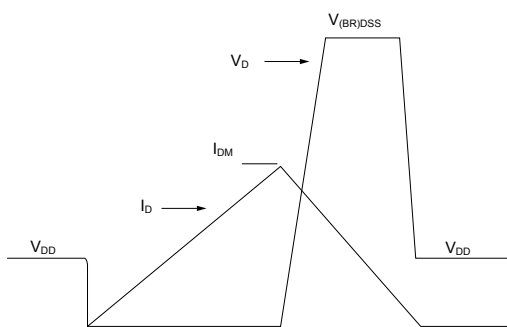
GADG180720181011SA

Figure 15. Test circuit for inductive load switching and diode recovery times


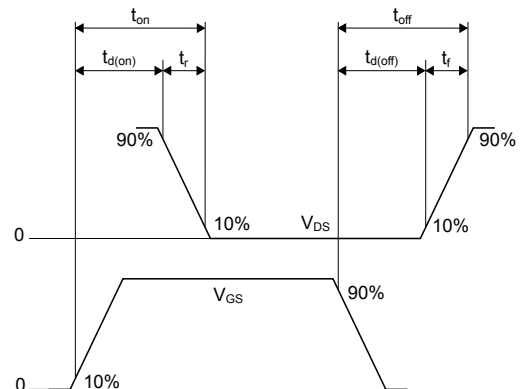
AM15857v1

Figure 16. Unclamped inductive load test circuit


AM15858v1

Figure 17. Unclamped inductive waveform


AM01472v1

Figure 18. Switching time waveform


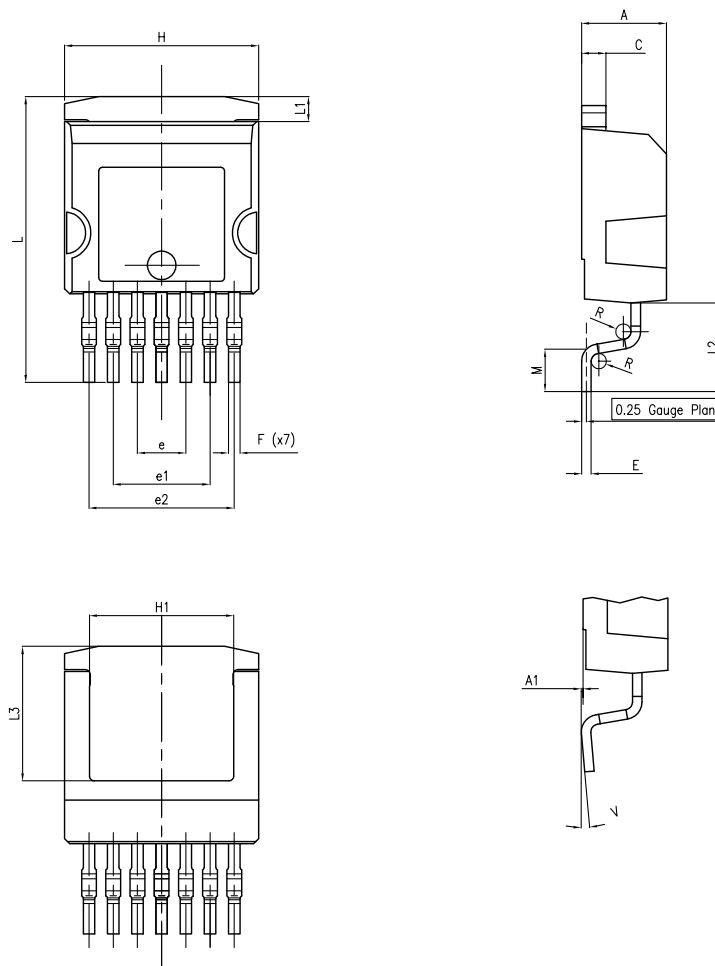
AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 H²PAK-7 package information

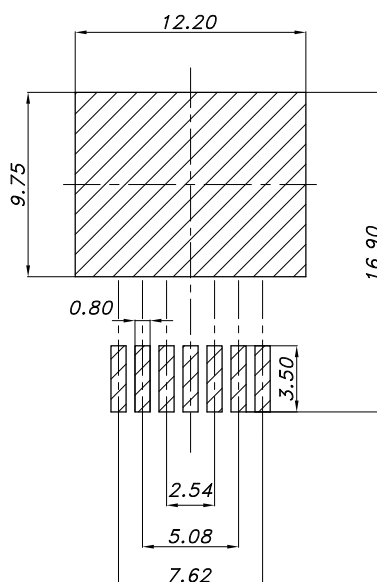
Figure 19. H²PAK-7 package outline



DM00249216_4

Table 8. H²PAK-7 package mechanical data

Dim.	mm	
	Min.	Max.
A	4.30	4.80
A1	0.03	0.20
C	1.17	1.37
e	2.34	2.74
e1	4.88	5.28
e2	7.42	7.82
E	0.45	0.60
F	0.50	0.70
H	10.00	10.40
H1	7.40	7.60
L	14.75	15.25
L1	1.27	1.40
L2	4.35	4.95
L3	6.85	7.25
M	1.90	2.50
R	0.20	0.60
V	0°	8°

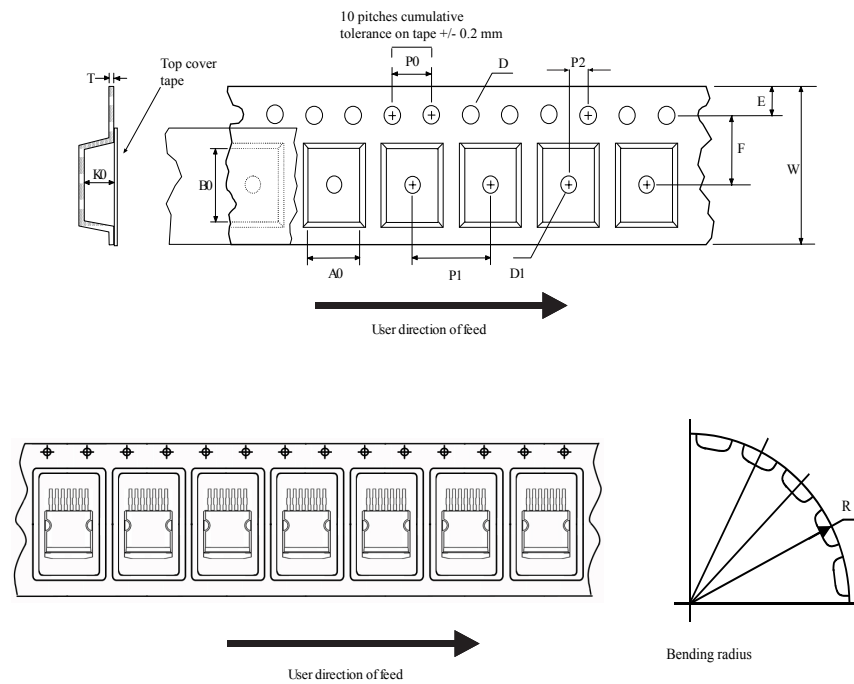
Figure 20. H²PAK-7 recommended footprint


footprint_DM00249216_4

Note: Dimensions are in mm.

4.2 Packing information

Figure 21. Tape outline



GADG160620211017SA

Figure 22. Reel outline

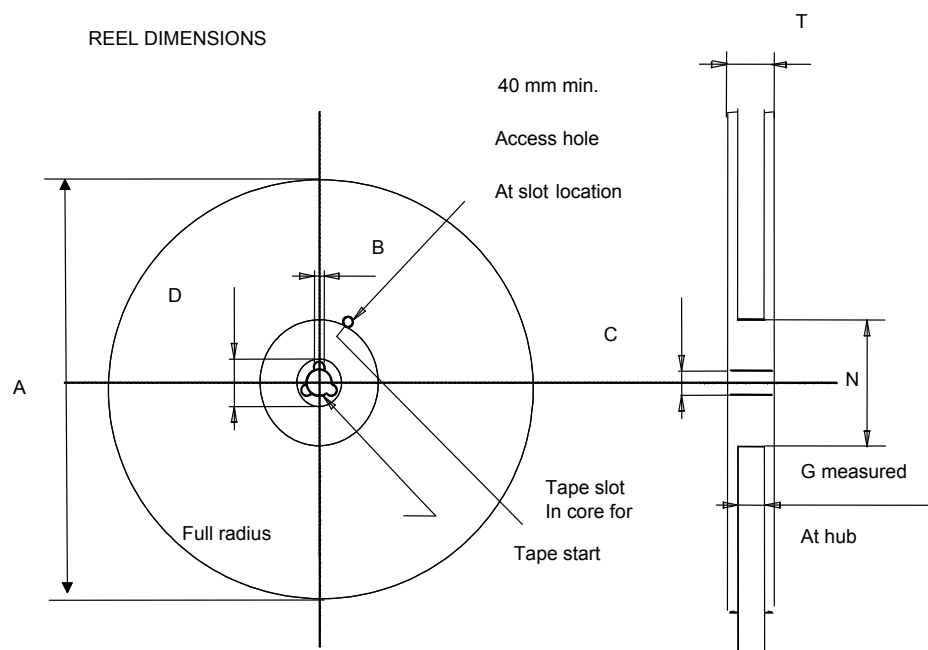


Table 9. Tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Revision history

Table 10. Document revision history

Date	Revision	Changes
01-Feb-2021	1	First release.
24-Jun-2021	2	Modified $R_{DS(on)}$ max. on cover page. Modified Table 1. Absolute maximum ratings, Table 2. Thermal data, Table 4. On/off-state and Table 7. Source-drain diode. Updated Section 3 Test circuits. Modified Figure 21. Tape outline. Minor text changes.

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